

App. No. 10/708,618
Amendment dated August 12, 2005
Reply to Office action of April 18, 2005

Amendments to the Specification (other than claims):

Please replace paragraph [0038] with the following amended paragraph:

[0038] The Q factor and electric field pattern (radiation pattern) for a cavity made from a donor-type point defect 4 as is illustrated in Fig. 1 were simulated by the FDTD method. The simulation parameters were configured by selecting silicon for the slab 1; and setting approximately $[1.55 \text{ } \mu\text{m}]$ 1.55 μm , which is generally used in optical communications, for the wavelength λ ; $[0.42 \text{ } \mu\text{m}]$ 0.42 μm for the lattice constant a ; $0.6a$ for the slab 1 thickness; and $0.29a$ for the predetermined sectional radius of the through-holes 2.